

100V N-Channel DTMOS

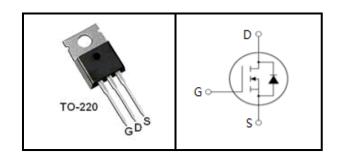
FEATURES

- Trench Power DTMOS technology
- Low R_{DS(ON)}
- Low Gate Charge
- Optimized for fast-switching applications

APPLICATIONS

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial

Device Marking and Package Information			
Device	Package	Marking	
TSP15N10A	TO-220	15N10A	





Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted				
Parameter	Symbol	Value	Unit	
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	100	V	
Continuous Drain Current (Package Limited)	I _D	150	А	
Pulsed Drain Current (note1) I _{DM}	600	А	
Gate-Source Voltage	V _{GSS}	±20	V	
Single Pulse Avalanche Energy (note2) E _{AS}	609	mJ	
Avalanche Current (note1) I _{AS}	28	Α	
Power Dissipation (T _C = 25°C)	P _D	208	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C	

Thermal Resistance				
Parameter	Symbol	Value	Unit	
Thermal Resistance, Junction-to-Case	R _{thJC}	0.6	°C/W	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	60	30/00	



Specifications T _J = 25°C, unless otherwise noted							
Parameter	Symbol Test Conditions	Took Conditions	Value			Unit	
r al allietei		Min.	Тур.	Max.	Offic		
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V	
Zero Gate Voltage Drain Current		$V_{DS} = 100V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μΑ	
Zero Gate Voltage Drain Gurrent	I _{DSS}	$V_{DS} = 100V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100		
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 20V$			±100	nA	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2		4	V	
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_{D} = 50A$		3.5	4.2	mΩ	
Forward Transconductance (Note3)	g _{fs}	$V_{DS} = 10V, I_{D} = 50A$		140		S	
Dynamic				-			
Input Capacitance	C _{iss}	\/ - 0\/		7700		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 50V,$		470			
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		28			
Total Gate Charge	Q_g			138		nC	
Gate-Source Charge	Q_{gs}	$V_{DD} = 50V, I_{D} = 50A,$ $V_{GS} = 10V$		37			
Gate-Drain Charge	Q_{gd}	55		35.5			
Turn-on Delay Time	t _{d(on)}			35			
Turn-on Rise Time	t _r	$V_{DD} = 50V, I_{D} = 50A,$		22			
Turn-off Delay Time	t _{d(off)}	$R_G = 25\Omega$		105		ns	
Turn-off Fall Time	t _f			45			
Drain-Source Body Diode Characteristics							
Continuous Body Diode Current	Is	T _C = 25°C			50	۸	
Pulsed Diode Forward Current	I _{SM}				150	A	
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}C$, $I_{SD} = 50A$, $V_{GS} = 0V$		0.9	1.2	V	
Reverse Recovery Time	t _{rr}	I _F = 50A,		50		ns	
Reverse Recovery Charge	Q _{rr}	di _F /dt = 500A/μs		110		nC	

Notes

- 1. Repetitive Rating: Pulse Width limited by maximum junction temperature
- 2. I_{AS} = 28A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1%



Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

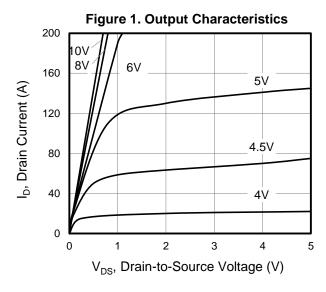


Figure 3. On-Resistance vs. Drain Current

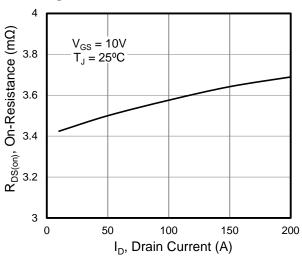
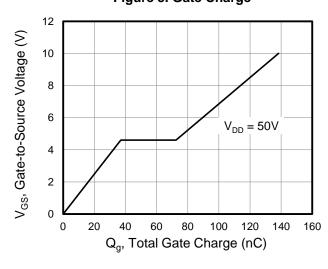
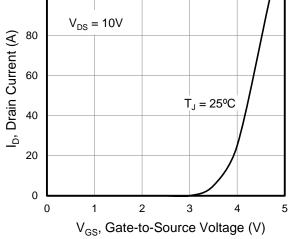


Figure 5. Gate Charge



 $V_{DS} = 10V$

Figure 2. Transfer Characteristics



100

Figure 4. Capacitance

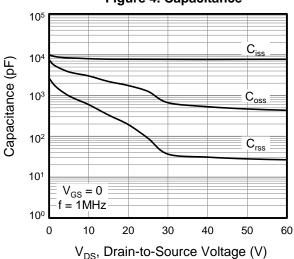
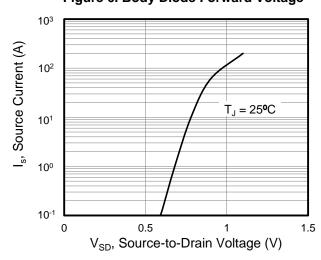


Figure 6. Body Diode Forward Voltage





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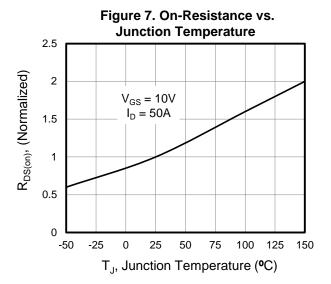


Figure 8. Threshold Voltage vs. Junction Temperature 1.2 1.1 V_{GS(th)}, (Variance) $I_{D} = 250 \mu A$ 1 0.9 8.0 0.7 0.6 0 50 -100 -50 100 150 200 T_J, Junction Temperature (°C)

Figure 9. Transient Thermal Impedance

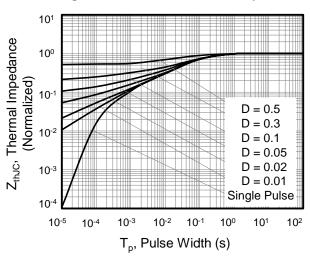




Figure A: Gate Charge Test Circuit and Waveform

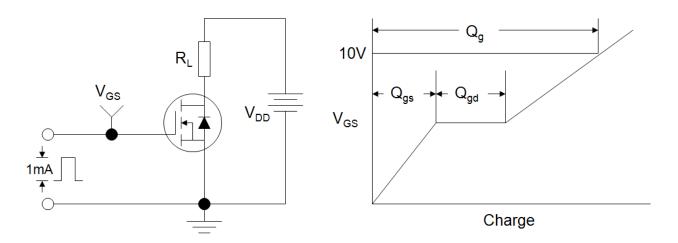


Figure B: Resistive Switching Test Circuit and Waveform

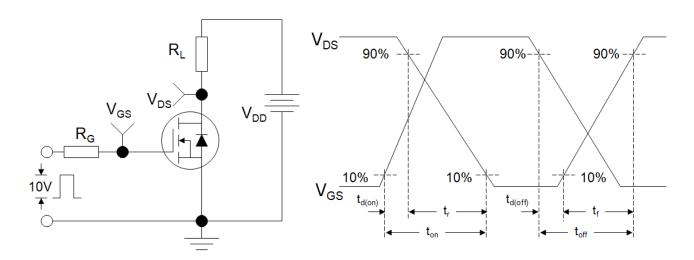
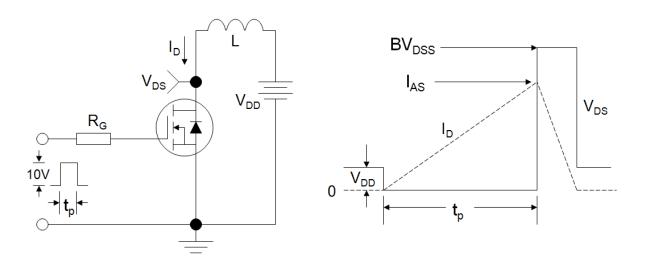
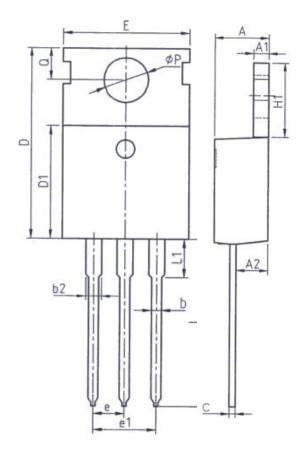


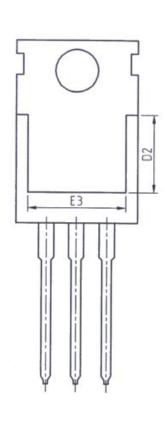
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-220





Unit: mm				
Symbol	Min.	Max.		
Α	4. 37	4. 77		
A1	1. 25	1. 45		
A2	2. 20	2. 60		
b	0. 70	0. 95		
b2	1. 17	1. 47		
С	0. 40	0. 65		
D	15. 10	16. 10		
D1	8. 80	9. 40		
D2	5. 50	_		

Unit: mm				
Symbol	Min.	Max.		
E	9. 70	10. 30		
E3	7. 00	-		
е	2. 54BSC			
e1	5. 08BSC			
H1	6. 25	6. 85		
L	12. 75	13.80		
L1	_	3. 40		
Р	3. 40	3. 80		
Q	2. 60	3. 00		



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